

To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: <http://www.renesas.com>

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors. Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (<http://www.renesas.com>).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

2SC5890

Silicon NPN Epitaxial
UHF / VHF wide band amplifier

RENESAS

ADE-208-1533 (Z)

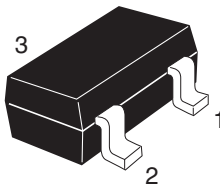
1st. Edition
Aug.2002

Features

- High gain bandwidth product:
 $f_T = 7.8$ GHz typ.
- High power gain and low noise figure;
PG = 12 dB typ., NF = 1.0 dB typ. at $f = 900$ MHz
- High collector power dissipation:
 $P_c = 700$ mW when using alumina ceramic board (25 x 60 x 0.7 mm)
- High withstanding to ESD of collector to emitter:
Withstand up to 700 V (only real value) at $C = 200$ pF, $R_s = 0$ condition.

Outline

MPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "FS-".

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	75	mA
Collector power dissipation	Pc	700*	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

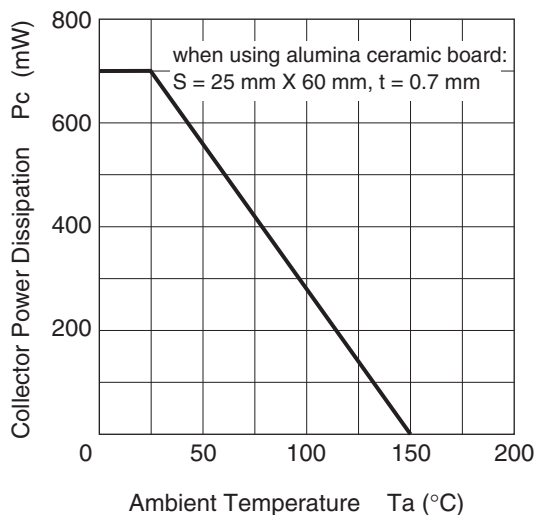
*When using alumina ceramic board (25 x 60 x 0.7 mm)

Electrical Characteristics

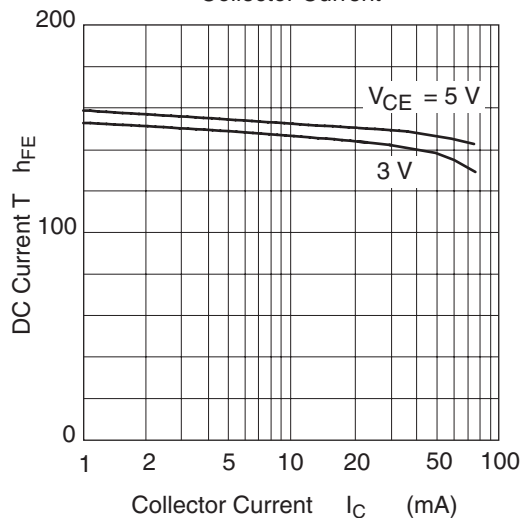
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 10\mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12 V, I_E = 0$
Collector cutoff current	I_{CEO}	—	—	1	mA	$V_{CE} = 9 V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5 V, I_C = 0$
DC current transfer ratio	h_{FE}	100	150	200	V	$V_{CE} = 5 V, I_C = 20 mA$
Collector output capacitance	Cob	—	0.9	1.5	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Reverse transfer capacitance	Cre	—	0.85	—	pF	$V_{CB} = 5 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	5.5	7.8	—	GHz	$V_{CE} = 5 V, I_C = 30 mA, f = 1 GHz$
Forward transfer coefficient	$ S_{21} ^2$	—	11	—	dB	$V_{CE} = 5 V, I_C = 30 mA, f = 1 GHz$
Power gain	PG	9.5	12	—	dB	$V_{CE} = 5 V, I_C = 30 mA, f = 900 MHz$
Noise figure	NF	—	1.0	1.9	dB	$V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz$

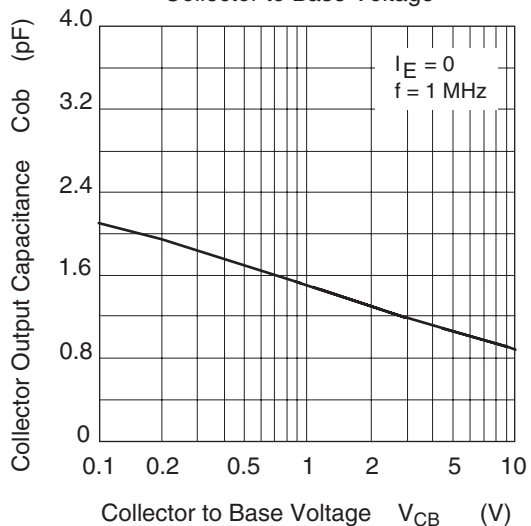
Collector Power Dissipation Curve



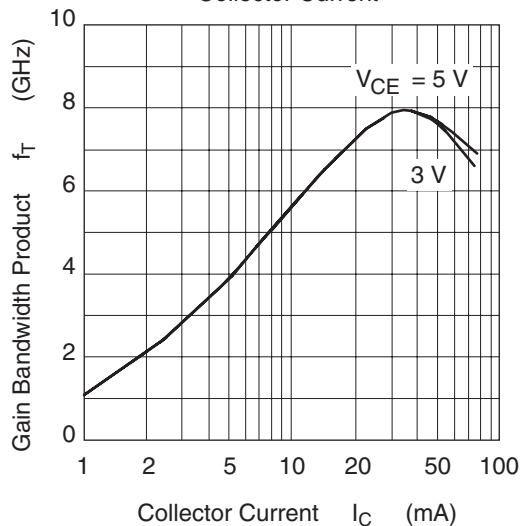
DC Current Transfer Ratio vs. Collector Current

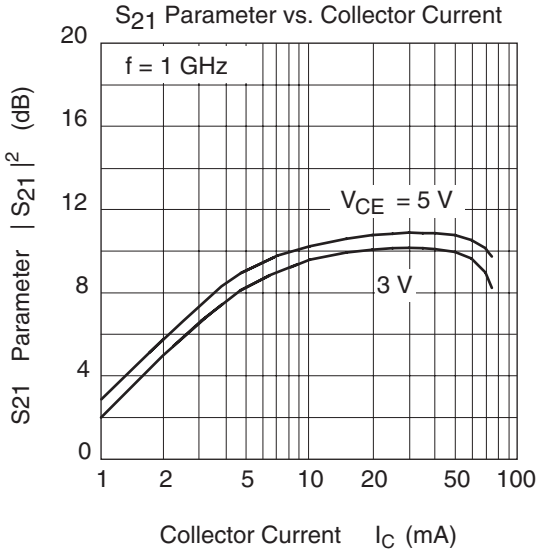
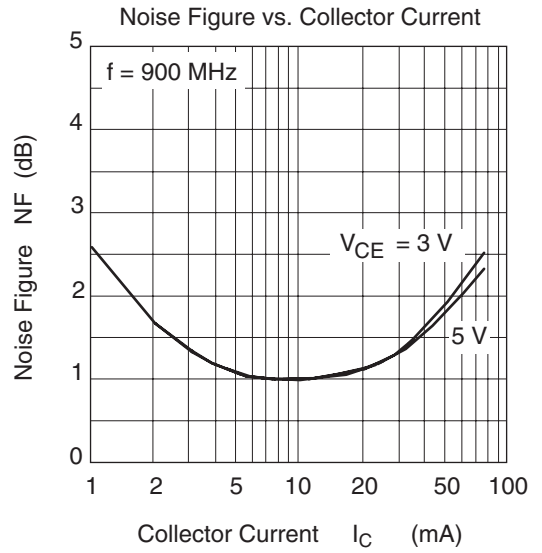
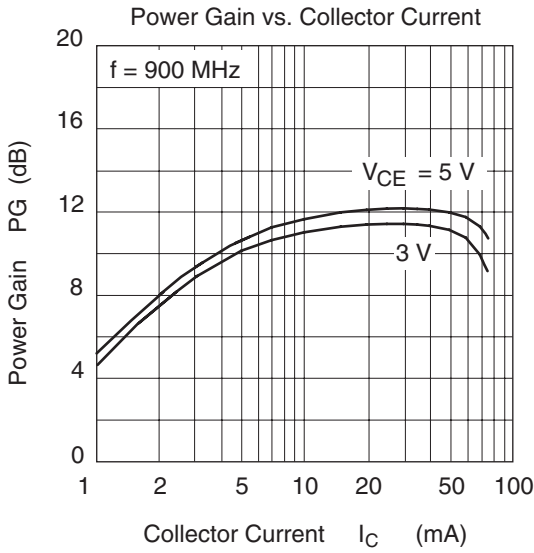


Collector Output Capacitance vs. Collector to Base Voltage

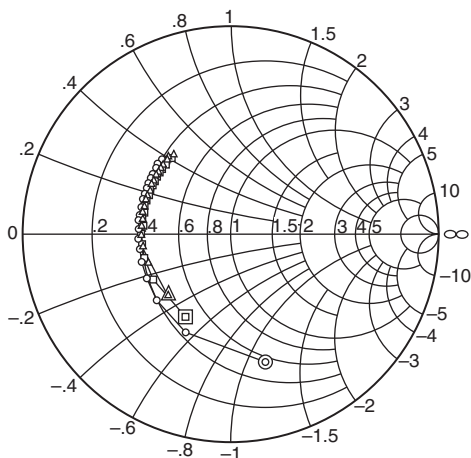


Gain Bandwidth Product vs. Collector Current





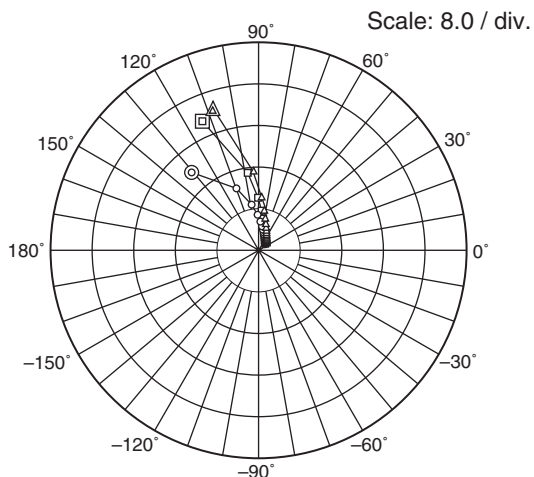
S11 Parameter vs. Frequency



Condition: $V_{CE} = 3\text{ V}$, $Z_O = 50\ \Omega$
100 to 2000 MHz (100 MHz Step)

- ⊙—○ ($I_C = 10\text{ mA}$)
- ⊠—□ ($I_C = 30\text{ mA}$)
- ▲—△ ($I_C = 50\text{ mA}$)

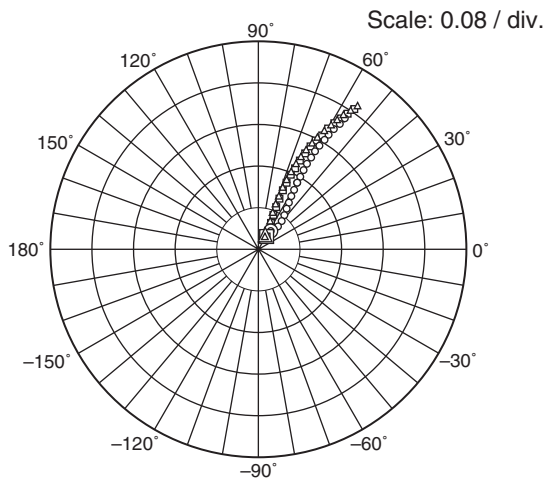
S21 Parameter vs. Frequency



Condition: $V_{CE} = 3\text{ V}$, $Z_O = 50\ \Omega$
100 to 2000 MHz (100 MHz Step)

- ⊙—○ ($I_C = 10\text{ mA}$)
- ⊠—□ ($I_C = 30\text{ mA}$)
- ▲—△ ($I_C = 50\text{ mA}$)

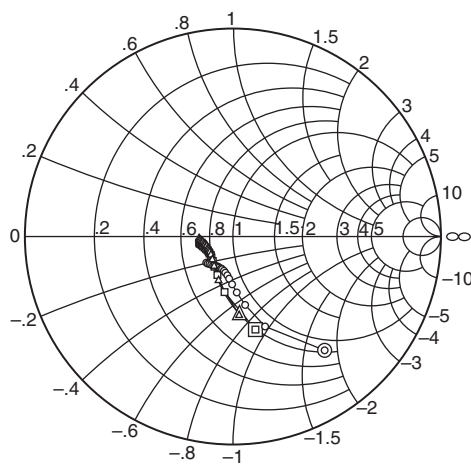
S12 Parameter vs. Frequency



Condition: $V_{CE} = 3\text{ V}$, $Z_O = 50\ \Omega$
100 to 2000 MHz (100 MHz Step)

- ⊙—○ ($I_C = 10\text{ mA}$)
- ⊠—□ ($I_C = 30\text{ mA}$)
- ▲—△ ($I_C = 50\text{ mA}$)

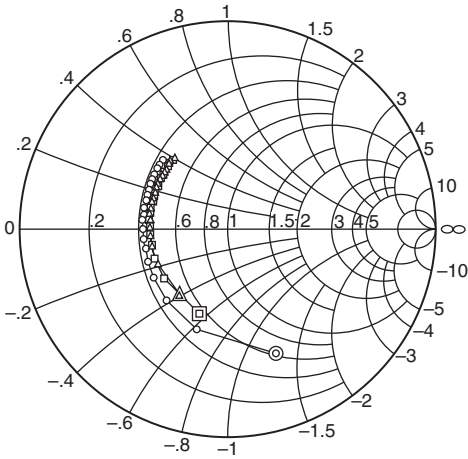
S22 Parameter vs. Frequency



Condition: $V_{CE} = 3\text{ V}$, $Z_O = 50\ \Omega$
100 to 2000 MHz (100 MHz Step)

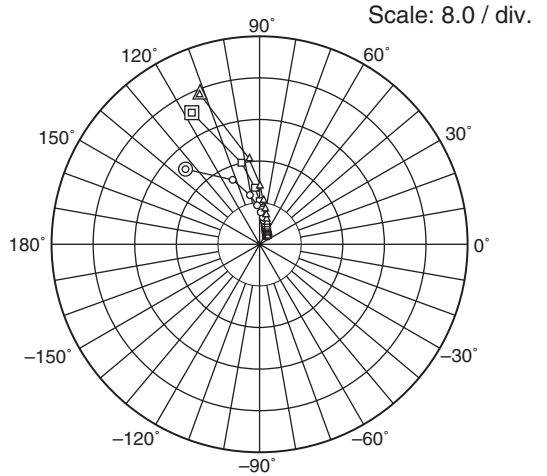
- ⊙—○ ($I_C = 10\text{ mA}$)
- ⊠—□ ($I_C = 30\text{ mA}$)
- ▲—△ ($I_C = 50\text{ mA}$)

S11 Parameter vs. Frequency



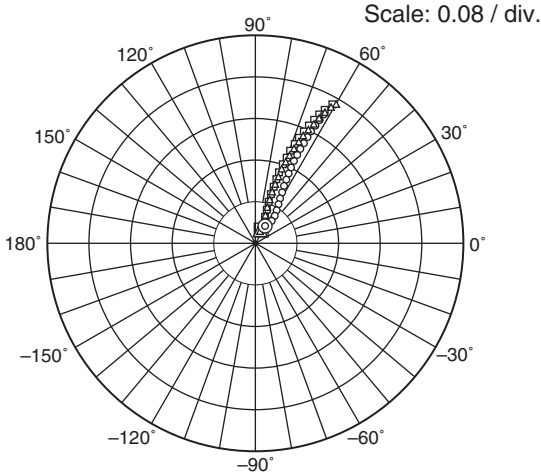
Condition: $V_{CE} = 5\text{ V}$, $Z_O = 50\ \Omega$
 100 to 2000 MHz (100 MHz Step)
 ○—○ ($I_C = 10\text{ mA}$)
 □—□ ($I_C = 30\text{ mA}$)
 ▲—▲ ($I_C = 50\text{ mA}$)

S21 Parameter vs. Frequency



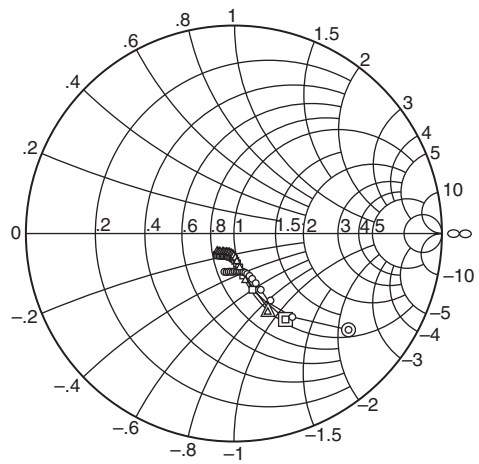
Condition: $V_{CE} = 5\text{ V}$, $Z_O = 50\ \Omega$
 100 to 2000 MHz (100 MHz Step)
 ○—○ ($I_C = 10\text{ mA}$)
 □—□ ($I_C = 30\text{ mA}$)
 ▲—▲ ($I_C = 50\text{ mA}$)

S12 Parameter vs. Frequency



Condition: $V_{CE} = 5\text{ V}$, $Z_O = 50\ \Omega$
 100 to 2000 MHz (100 MHz Step)
 ○—○ ($I_C = 10\text{ mA}$)
 □—□ ($I_C = 30\text{ mA}$)
 ▲—▲ ($I_C = 50\text{ mA}$)

S22 Parameter vs. Frequency



Condition: $V_{CE} = 5\text{ V}$, $Z_O = 50\ \Omega$
 100 to 2000 MHz (100 MHz Step)
 ○—○ ($I_C = 10\text{ mA}$)
 □—□ ($I_C = 30\text{ mA}$)
 ▲—▲ ($I_C = 50\text{ mA}$)

S parameter(VCE = 3V, I_c = 10 mA, Z_o = 50 Ω)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.635	-75.2	19.73	130.5	0.042	55.9	0.698	-51.2
200	0.524	-115.1	12.64	109.7	0.058	49.5	0.455	-70.6
300	0.483	-138.4	8.86	98.7	0.071	50.6	0.330	-80.4
400	0.462	-152.3	6.82	91.6	0.083	52.8	0.266	-86.8
500	0.454	-162.6	5.51	86.4	0.096	55.2	0.226	-91.9
600	0.448	-170.5	4.63	81.9	0.108	56.8	0.201	-96.3
700	0.451	-176.9	4.01	78.0	0.121	58.2	0.185	-99.5
800	0.448	177.1	3.54	74.2	0.134	59.0	0.175	-103.3
900	0.453	171.7	3.17	71.5	0.149	59.8	0.169	-106.3
1000	0.452	168.6	2.87	68.2	0.162	60.0	0.163	-109.9
1100	0.453	163.6	2.63	65.1	0.176	60.3	0.161	-112.3
1200	0.459	158.8	2.43	62.5	0.190	60.4	0.162	-116.0
1300	0.460	155.4	2.27	59.8	0.204	60.1	0.160	-118.1
1400	0.464	151.8	2.13	57.4	0.218	60.0	0.162	-121.1
1500	0.469	148.8	2.00	54.8	0.232	59.5	0.162	-124.7
1600	0.474	145.5	1.89	52.2	0.246	58.8	0.167	-126.3
1700	0.477	143.0	1.80	49.9	0.260	58.6	0.169	-129.4
1800	0.482	139.0	1.72	47.9	0.274	57.9	0.172	-132.4
1900	0.491	136.7	1.65	45.6	0.288	57.1	0.177	-134.6
2000	0.490	133.2	1.59	43.5	0.302	56.6	0.179	-137.2

2SC5890

($V_{CE} = 3V$, $I_C = 30\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.449	-118.4	27.19	113.3	0.029	57.1	0.459	-76.8
200	0.431	-150.0	15.04	98.0	0.043	61.4	0.270	-98.5
300	0.429	-165.1	10.09	90.5	0.060	65.3	0.199	-112.0
400	0.428	-174.1	7.63	85.6	0.076	67.0	0.170	-121.5
500	0.430	179.3	6.12	81.7	0.093	67.6	0.152	-129.4
600	0.421	174.0	5.12	78.2	0.110	67.9	0.144	-135.4
700	0.431	169.6	4.42	75.3	0.126	67.8	0.139	-139.6
800	0.428	165.6	3.89	72.2	0.143	67.4	0.138	-144.1
900	0.438	161.3	3.48	69.8	0.160	66.9	0.137	-146.7
1000	0.436	157.8	3.15	66.9	0.176	65.9	0.138	-150.7
1100	0.436	154.0	2.88	64.2	0.193	65.3	0.138	-152.5
1200	0.445	150.5	2.66	62.3	0.209	64.3	0.142	-155.5
1300	0.446	147.5	2.49	59.7	0.225	63.4	0.141	-157.2
1400	0.446	144.6	2.33	57.5	0.240	62.5	0.146	-159.1
1500	0.451	141.6	2.19	55.0	0.256	61.2	0.148	-162.0
1600	0.454	138.6	2.07	53.0	0.272	60.2	0.151	-162.2
1700	0.457	136.2	1.98	50.6	0.287	59.3	0.155	-164.6
1800	0.459	132.6	1.88	49.0	0.301	58.2	0.158	-166.8
1900	0.473	130.7	1.80	46.6	0.317	57.0	0.163	-167.7
2000	0.465	127.4	1.73	44.9	0.331	55.9	0.165	-169.7

($V_{CE} = 3V$, $I_C = 50 \text{ mA}$, $Z_o = 50 \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.424	-136.3	28.25	108.0	0.025	60.4	0.382	-86.3
200	0.426	-160.8	15.12	94.5	0.041	65.8	0.225	-108.8
300	0.433	-171.8	10.08	88.0	0.058	69.0	0.172	-122.9
400	0.437	-179.2	7.59	83.5	0.076	70.1	0.152	-132.5
500	0.440	175.1	6.09	80.1	0.093	70.2	0.141	-140.5
600	0.435	170.8	5.08	76.8	0.110	69.9	0.138	-146.0
700	0.443	166.5	4.39	73.9	0.128	69.4	0.134	-149.8
800	0.441	162.8	3.86	70.9	0.145	68.6	0.135	-153.3
900	0.446	158.4	3.44	68.4	0.163	67.8	0.136	-155.4
1000	0.447	155.7	3.11	65.9	0.179	66.8	0.138	-159.5
1100	0.444	152.5	2.86	63.3	0.196	65.9	0.138	-160.9
1200	0.455	148.4	2.64	61.0	0.212	64.8	0.143	-163.1
1300	0.455	145.9	2.47	58.5	0.229	63.6	0.142	-164.6
1400	0.463	142.3	2.31	56.5	0.244	62.7	0.147	-166.3
1500	0.462	140.1	2.17	54.0	0.261	61.3	0.151	-169.0
1600	0.466	137.4	2.05	51.9	0.276	60.3	0.153	-169.0
1700	0.469	135.1	1.97	50.0	0.291	59.1	0.157	-171.3
1800	0.474	131.2	1.87	48.3	0.306	58.0	0.161	-173.0
1900	0.481	129.6	1.79	46.0	0.321	56.7	0.165	-173.5
2000	0.476	126.4	1.72	44.0	0.336	55.6	0.166	-176.0

2SC5890

($V_{CE} = 5V$, $I_C = 10\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.643	-69.1	20.28	134.6	0.038	60.7	0.719	-40.0
200	0.512	-107.8	13.36	113.9	0.053	54.0	0.485	-55.1
300	0.460	-130.9	9.51	102.7	0.064	54.8	0.362	-61.6
400	0.433	-146.9	7.33	95.6	0.075	57.2	0.295	-64.8
500	0.421	-157.7	5.96	90.2	0.087	59.4	0.256	-66.7
600	0.411	-166.4	5.01	85.6	0.098	61.2	0.230	-68.5
700	0.414	-173.0	4.34	81.7	0.111	62.2	0.212	-70.4
800	0.414	-179.6	3.83	78.0	0.123	63.5	0.200	-72.5
900	0.419	174.3	3.43	75.0	0.136	64.1	0.192	-74.5
1000	0.414	170.8	3.10	71.8	0.149	64.5	0.186	-76.9
1100	0.421	166.3	2.84	68.8	0.161	64.8	0.182	-78.9
1200	0.420	161.3	2.63	66.0	0.175	64.9	0.180	-81.9
1300	0.424	157.6	2.45	63.3	0.188	64.7	0.178	-84.6
1400	0.428	154.2	2.29	61.2	0.201	64.6	0.179	-87.2
1500	0.435	150.5	2.16	58.4	0.214	64.2	0.178	-90.2
1600	0.439	147.4	2.03	56.0	0.227	63.9	0.180	-93.1
1700	0.444	144.2	1.94	53.8	0.240	63.6	0.181	-96.2
1800	0.450	140.1	1.85	51.5	0.254	63.0	0.182	-99.2
1900	0.454	137.5	1.77	49.4	0.267	62.5	0.185	-102.2
2000	0.458	134.0	1.69	47.3	0.281	62.0	0.187	-105.3

($V_{CE} = 5V$, $I_C = 30\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.430	-108.9	28.25	118.1	0.026	61.8	0.482	-59.0
200	0.387	-142.7	16.05	102.5	0.040	65.5	0.283	-72.0
300	0.380	-158.5	10.90	94.7	0.055	69.2	0.205	-77.8
400	0.374	-168.7	8.27	89.8	0.070	70.7	0.165	-81.7
500	0.375	-176.5	6.67	85.8	0.085	71.8	0.143	-84.6
600	0.376	177.6	5.59	82.3	0.101	72.1	0.130	-87.9
700	0.384	172.9	4.82	79.4	0.116	71.7	0.121	-90.6
800	0.383	167.8	4.24	76.5	0.131	71.6	0.116	-93.5
900	0.388	164.0	3.78	73.8	0.147	71.3	0.112	-96.9
1000	0.385	159.5	3.43	70.9	0.162	70.6	0.111	-99.9
1100	0.390	155.7	3.13	68.4	0.177	69.7	0.111	-102.7
1200	0.398	152.4	2.90	66.2	0.192	69.2	0.111	-106.2
1300	0.396	148.1	2.70	63.8	0.207	68.2	0.112	-108.8
1400	0.406	146.2	2.53	61.7	0.221	67.4	0.114	-111.8
1500	0.407	142.5	2.37	59.2	0.236	66.4	0.115	-115.0
1600	0.408	139.8	2.25	57.1	0.250	65.4	0.118	-117.5
1700	0.414	137.8	2.13	54.9	0.265	64.4	0.122	-120.7
1800	0.420	133.6	2.04	53.1	0.278	63.5	0.124	-123.7
1900	0.428	131.5	1.94	50.9	0.292	62.5	0.128	-126.6
2000	0.427	128.4	1.86	49.2	0.306	61.3	0.131	-129.1

2SC5890

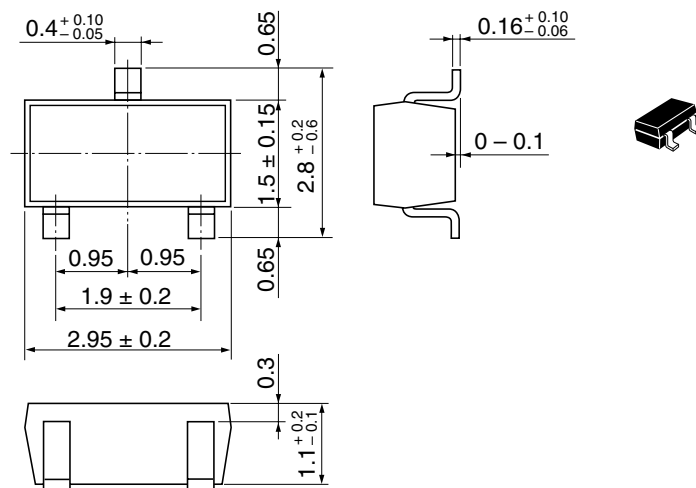
($V_{CE} = 5V$, $I_C = 50\text{ mA}$, $Z_o = 50\ \Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.392	-125.2	30.12	111.6	0.023	62.6	0.411	-67.0
200	0.380	-153.9	16.44	97.6	0.037	67.6	0.235	-78.0
300	0.379	-167.5	11.03	90.8	0.053	70.8	0.170	-82.6
400	0.380	-175.1	8.33	86.2	0.069	72.1	0.139	-86.5
500	0.381	178.8	6.68	82.5	0.085	72.2	0.121	-89.3
600	0.381	173.2	5.59	79.4	0.100	72.3	0.111	-93.0
700	0.390	168.9	4.82	76.5	0.116	71.7	0.105	-95.3
800	0.389	165.1	4.25	73.5	0.132	71.1	0.102	-98.9
900	0.394	160.4	3.79	71.2	0.148	70.7	0.101	-101.5
1000	0.393	157.7	3.43	68.6	0.163	69.7	0.100	-105.7
1100	0.396	153.6	3.13	66.0	0.178	69.0	0.100	-107.8
1200	0.403	150.0	2.89	63.8	0.193	67.9	0.103	-111.8
1300	0.407	147.4	2.70	61.4	0.209	67.0	0.103	-113.8
1400	0.410	144.0	2.52	59.2	0.223	66.1	0.106	-117.1
1500	0.411	141.2	2.36	57.0	0.238	65.0	0.108	-120.5
1600	0.414	138.5	2.25	54.9	0.253	64.0	0.113	-122.6
1700	0.416	136.4	2.13	52.6	0.267	63.0	0.115	-125.9
1800	0.428	132.5	2.03	50.6	0.281	62.0	0.118	-128.8
1900	0.436	130.7	1.94	48.6	0.295	60.9	0.123	-131.2
2000	0.431	127.3	1.87	46.8	0.309	59.8	0.124	-134.1

Package Dimensions

As of January, 2002

Unit: mm



Hitachi Code	MPAK(T)
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.011 g

Disclaimer

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

Sales Offices**HITACHI****Hitachi, Ltd.**

Semiconductor & Integrated Circuits
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL <http://www.hitachisemiconductor.com/>

For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe Ltd.
 Electronic Components Group
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585200

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen
 Postfach 201, D-85619 Feldkirchen
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00
 Singapore 049318
 Tel: <65>-6538-6533/6538-8577
 Fax: <65>-6538-6933/6538-3877
 URL: <http://semiconductor.hitachi.com.sg>

Hitachi Asia Ltd.
 (Taipei Branch Office)
 4/F, No. 167, Tun Hwa North Road
 Hung-Kuo Building
 Taipei (105), Taiwan
 Tel: <886>-(2)-2718-3666
 Fax: <886>-(2)-2718-8180
 Telex: 23222 HAS-TP
 URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon Hong Kong
 Tel: <852>-2735-9218
 Fax: <852>-2730-0281
 URL: <http://semiconductor.hitachi.com.hk>

Copyright © Hitachi, Ltd., 2002. All rights reserved. Printed in Japan.

Colophon 6.0